NSN 5962-01-292-9189

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View Online at https://aerobasegroup.com/nsn/5962-01-292-9189

0.840 inches	
Body Width:	
Between 0.220 inches	and 0.310 inches
Body Height:	
0.185 inches	
Maximum Power Dise	sipation Rating:
739.0 milliwatts	
Operating Tempuratu	ire Range:
-55.0/+125.0 degrees	celsius
Storage Tempurature	Range:
-65.0/+150.0 degrees	celsius
Features Provided:	
Schottky and program	mable and monolithic and bipolar and 3-state output
Inclosure Material:	
Ceramic	
Inclosure Configurati	ion:
Dual-in-line	
Output Logic Form:	
Transistor-transistor lo	gic
Input Circuit Pattern:	
6 input	
Case Outline Source	And Designator:
D-2 mil-m-38510	
Terminal Surface Tre	atment:
Solder	
Voltage Rating And T	Type Per Characteristic:
7.0 volts power source	9
Time Rating Per Cha	cteristic:
80.00 nanoseconds p	ropagation delay time, low to high level output and 80.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type	e de la companya de l
Rom	
Test Data Document:	
96906-mil-std-883 star	ndard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Q	luantity:
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Yes - demil/mli

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